

Supplementary Information

Hierarchical hollow structure of Ni_xCo_{3-x}O₄ particles for high-performance hybrid supercapacitors with excellent cyclic stability

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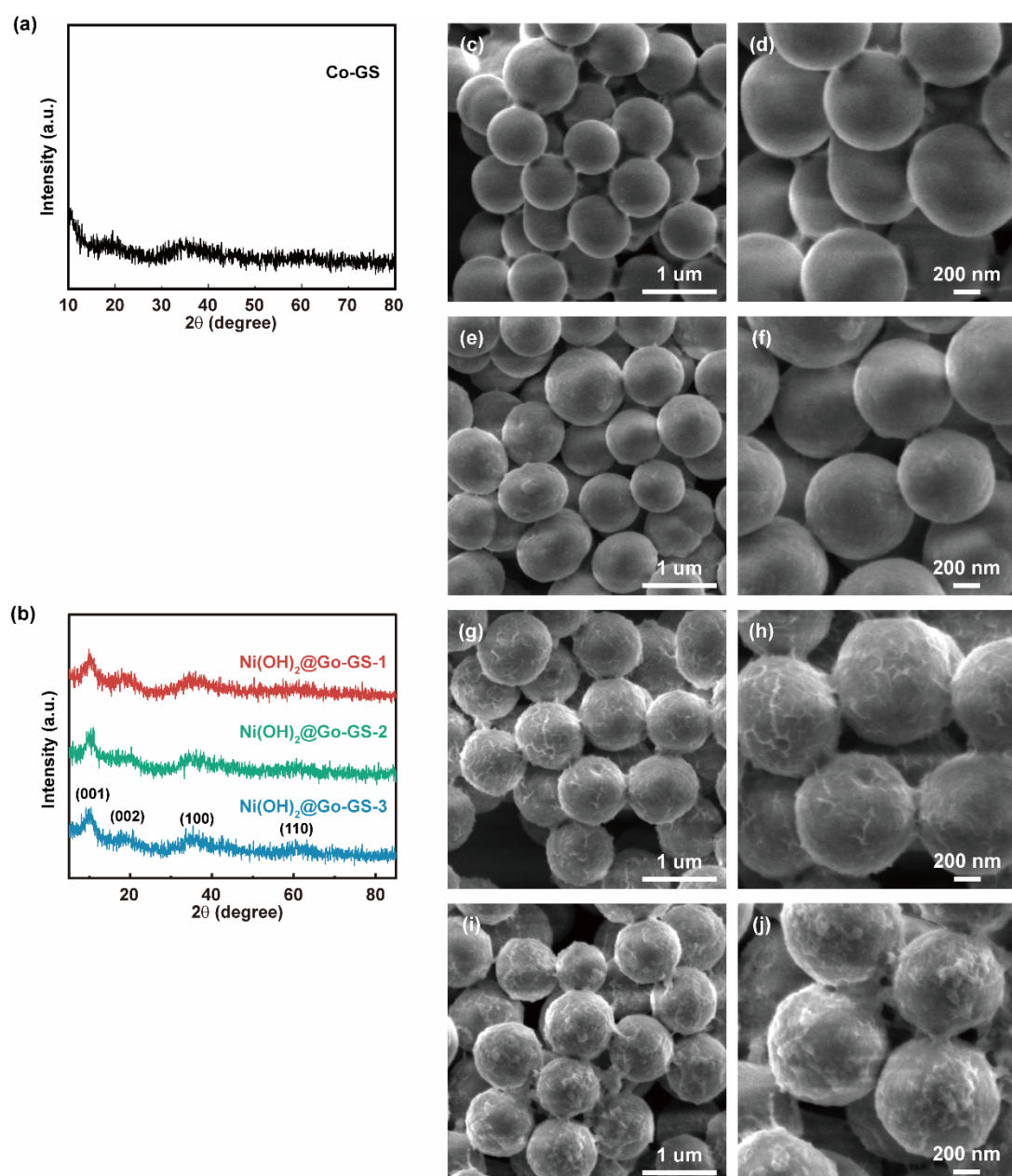


Figure S1 (a, b) XRD diffraction pattern of Co-GSs and Ni(OH)₂@Co-GS; SEM images of (c, d) Co-GSs; (e, f) Ni(OH)₂@Co-GS-1; (g, h) Ni(OH)₂@Co-GS-2; (i, j) Ni(OH)₂@Co-GS-3.

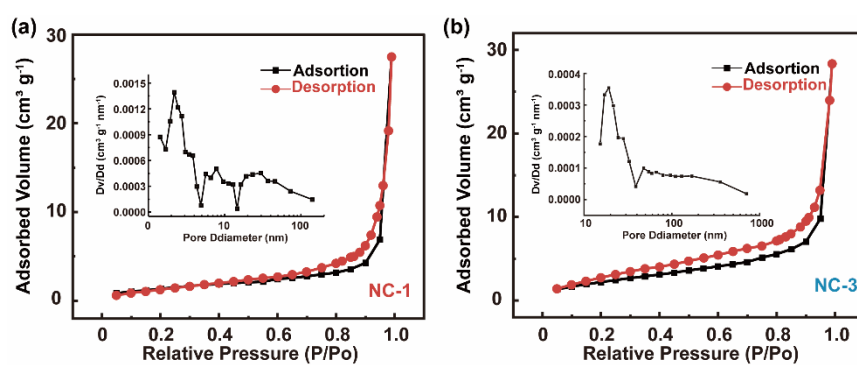


Figure S2 N₂ adsorption-desorption isotherms and corresponding pore size distribution (inset) of (a) NC-HHP-1 and (b) NC-HHP-3.

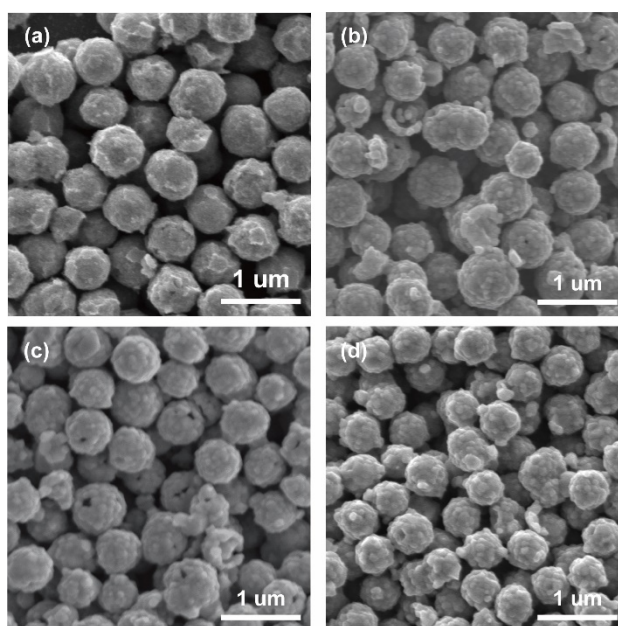


Figure S3 SEM images of NC-HHP-2 at different annealing temperatures: (a) 300 °C; (b) 400 °C; (c) 500 °C; (d) 600 °C.

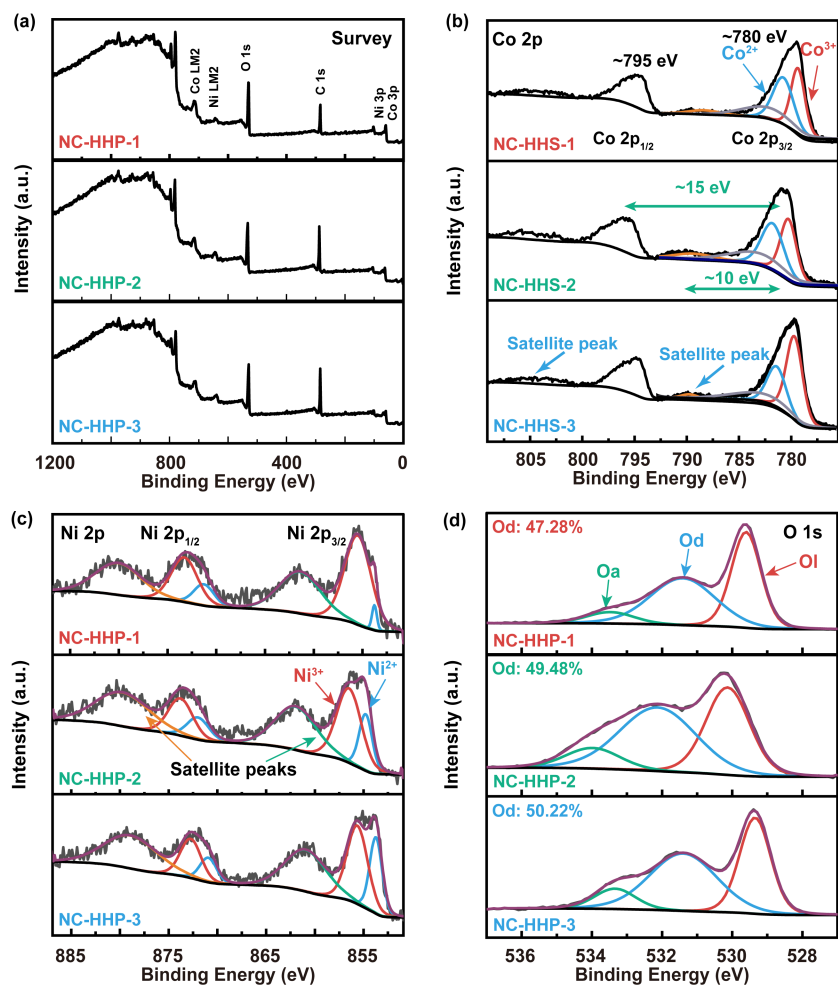


Figure S4 XPS spectra of NC-HHPs.

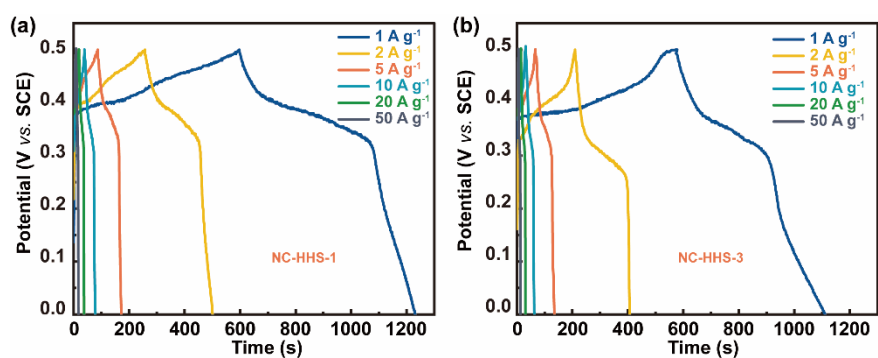


Figure S5 GCD curves of (a) NC-HHP-1 and (b) NC-HHP-3 at various current densities.

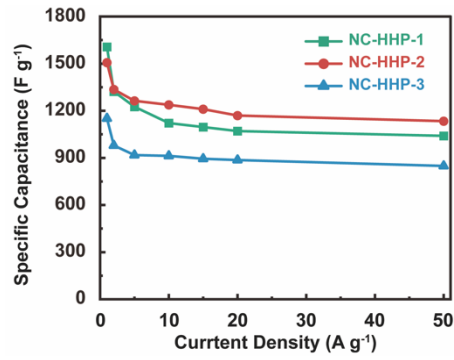


Figure S6 Corresponding specific capacitance of NC-HHPs by using $F g^{-1}$ as the unit.

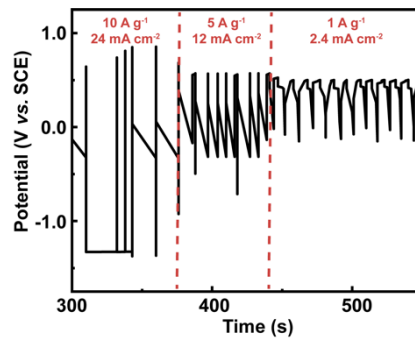


Figure S7 GCD curves of the blank Ni foam sample at different current densities.

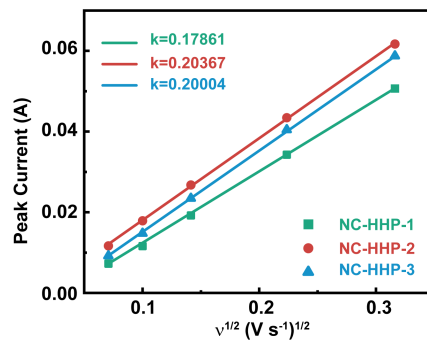


Figure S8 Plot of peak current vs. $v^{1/2}$ to calculate diffusion coefficient.

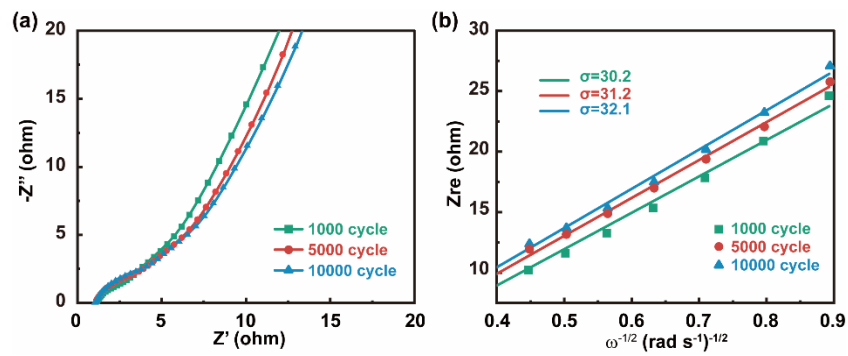


Figure S9 (a) Nyquist plots of HSC device after different cycle; (b) the linear relationship between Z_{re} and $\omega^{-1/2}$ of HSC device after different cycle.

Method to calculate voltametric charge

Trasatti pioneered a method to quantify the surface contribution. As explained by Mousavi and Augustyn,^{1,2} the voltammetric charge is related to the scan rate. The value of $q(v)$ can be deconvoluted into two terms: $q_{s,total}$ (surface-controlled) and q_d (diffusion-controlled). Then, the surface-controlled component can be further divided into two terms: (1) " $q_{s,out}$ ", represents the contribution of the outer surface of the electrode active material to the charge storage (more accessible position such as the region directly accessible to the electrolyte), which is invariant of sweep rate.^{1,2} (2) " $q_{s,in}$ ", comes from the partially accessible sites (less accessible position such as pores, grain boundaries, and cracks), which is sweep rate dependent.^{1,2}

When the scan rate tends to infinity, the part of $q_{s,in}$ equals 0:

$$q = q_{s,out} + q_d \quad \text{A}$$

When the scan rate tends to 0:

$$q = q_{s,in} + q_{s,out} + q_d \quad \text{B}$$

With these boundary conditions, $q_{s,in}$ and $q_{s,out}$ can be calculated by plotting the relationship between the voltammetric charge and the scan rate as below:

(1) $q_{s,out}$: Assuming semi-infinite linear diffusion and a linear relationship between q_d and $v^{-1/2}$, when the scan rate tends to infinity, eq A can be rewritten as: $q = q_{s,out} + k_1 v^{-1/2}$. So when v tends to infinity, that is, $v^{-1/2}$ tends to 0, using the relationship between q and $v^{-1/2}$, we can get the intercept, which is $q_{s,out}$.²

(2) $q_{s,in}$: Assuming q^{-1} decreases linearly with $v^{1/2}$, eq B can be rewritten as:

$q^{-1} = (q_{s,in} + q_{s,out})^{-1} + k_2 v^{1/2}$. So when v tends to 0, that is, $v^{1/2}$ tends to 0, using the relationship between q^{-1} and $v^{1/2}$, we can get the intercept, which is $(q_{s,total})^{-1}$. $q_{s,in}$ then can be obtained by using eq: $q_{s,total} = q_{s,in} + q_{s,out}$.²

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Table S1 ICP-OES results of NC-HHP.

NC-HHP	Co (wt%)	Ni (wt%)	O (wt%)	Co (at%)	Ni (at%)	Ni (at%)/ Co (at%)
1	58.78	18.02	23.20	36.21	11.15	0.31
2	56.73	19.53	23.74	34.64	11.97	0.35
3	54.85	20.16	24.99	32.82	12.11	0.37

Table S2 Specific surface area and pore size data for NC-HHP.

NC-HHP	Surface Area		Pore Size	
	Multi BET (m ² g ⁻¹)	Langmuir (m ² g ⁻¹)	Average (nm)	BJH (nm)
1	5.3	9.2	32.0	2.2
2	12.8	22.5	89.3	17.0
3	8.8	14.9	99.6	19.1

Table S3 XPS analysis results of NC-HHP.

NC-HHP	Co	Ni	O
1	1	0.33	3.30
2	1	0.48	4.01
3	1	0.65	5.15

Table S4 Parameters from equivalent circuit model of NC-HHP.

NC-HHP	Rs	R1	Rct
1	0.41	7.8	52.9
2	0.43	3.4	37.1
3	0.38	8.6	92.0

Table S5 Specific parameter value of diffusion coefficient from EIS.

	NC-HHP-1	NC-HHP-2	NC-HHP-3
R (J mol ⁻¹ K ⁻¹)		8.314	
T (K)		298	
A (cm ²)		1	
n		1	
F (C mol ⁻¹)		96500	
c (mol cm ³)		0.006	
σ	27.72	27.10	28.02

Table S6 Diffusion coefficients calculated by using EIS data.

Electrode materials	Diffusion coefficient	Ref
NC-HHP-1	1.28×10^{-12}	This work
NC-HHP-2	1.34×10^{-12}	This work
NC-HHP-3	1.25×10^{-12}	This work
NiCo ₂ O ₄ thin films	4.6×10^{-13}	[1]
Ni _x Co _{3-x} O ₄ thin films	1.45×10^{-17}	[1]
Co-doped MnO ₂	1.58×10^{-13}	[2]
Layered NiCo(OH) ₄	5.50×10^{-12}	[3]
Alkali etching CoSi-3	1.83×10^{-13}	[4]
Hierarchical CoFe ₂ O ₄ nanorods	1.30×10^{-9}	[5]
Co ₃ (PO ₄) ₂ nanoflakes	5.52×10^{-9}	[6]
mesoporous STP	3.27×10^{-13}	[7]

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Table S7 Diffusion coefficients calculated by using CV data

Electrode materials	Diffusion coefficient	Ref
NC-HHP-1	1.22×10^{-8}	This work
NC-HHP-2	1.59×10^{-8}	This work
NC-HHP-3	1.54×10^{-8}	This work
NiCo ₂ O ₄ @rGO	2.43×10^{-8}	[1]
Co ₃ O ₄ /NiO	1.60×10^{-12}	[2]
NiCo ₂ O ₄ /NF	5.80×10^{-12}	[3]
NiCo ₂ O ₄ /NF@PPy	8.20×10^{-12}	[3]
NiCo ₂ O ₄ nanobelt	3.40×10^{-13}	[4]
NixCo _{3-x} O ₄ nanobelt	4.60×10^{-13}	[4]
Co ₃ O ₄ nanoneedle	8.55×10^{-11}	[5]
Co ₃ O ₄ /Carbon paper	5.20×10^{-11}	[6]
S-doped Co ₃ O ₄	1.21×10^{-9}	[7]
Ni-Co-OH@Graphene	1.47×10^{-10}	[8]
CoNiP nanocrystals	2.64×10^{-10}	[9]
NiFe ₂ O ₄ /rGO	2.60×10^{-12}	[10]

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Table S8 Comparison of the capacitance and cyclic stability data of NC-HHP with published work.

Electrode	Current density (A g ⁻¹)	Specific capacity (F g ⁻¹)	Cycling stability	Reference
Hierarchical hollow Ni_xCo_{3-x}O₄ particles	10	1192	99%@40000 cycles	This work
NiCo ₂ O ₄ nanoneedles	10	820	114%@1000 cycles	[1]
NiCo ₂ O ₄ -CNT nanoparticles	5	557	89.3%@5000 cycles	[2]
Hierarchical Ni(OH) ₂ nanoflakes	5	508	65.0%@4500 cycles	[3]
N-doped carbon@NiCo ₂ O ₄ nanowire	10	984	91.3%@5000 cycles	[4]
NiO@Co ₃ O ₄ @graphene quantum dots	10	748	76.4%@3000 cycles	[5]
Multilevel NiCo ₂ O ₄ /Ni nanoporous	10	708	90.8%@5000 cycles	[6]
CC/NiCo ₂ O ₄ @NiO nanosheets	6.15	690	90.9%@10000 cycles	[7]
NiCo ₂ O ₄ nanosheets	10	1093	85.8%@10000 cycles	[8]
Hexagonal NiCo ₂ O ₄ nanostructures	10	600	98.0%@2000 cycles	[9]
Ultrathin NiCo ₂ O ₄ nanosheets	10	635	91.4%@5000 cycles	[10]
Core-shell NiCo ₂ O ₄ @Ni _x Co _y MoO ₄	5	826	99.5%@10000 cycles	[11]
Core-shell NiCo ₂ O ₄ @NiCo ₂ O ₄ nanocones	4	887	85.3%@21000 cycles	[12]
Yolk-shelled NiCo ₂ O ₄ spheres	10	558	98.0%@10000 cycles	[13]

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Table S9 Comparison of the capacitance and cyclic stability data of NC-HHP//AC HSC device with other transition metal oxides based hybrid supercapacitors.

Electrode	Current density (A g ⁻¹)	Specific capacity (F g ⁻¹)	Cycling stability	Reference
NC-HHP//AC	10	161	~100%@50000 cycles	This work
NiS-NiCo ₂ O ₄ @C//AC	2	82.5	89%@5000 cycles	[1]
NiCo ₂ O ₄ @HfC//AC	10	132.7	94.8%@5000 cycles	[2]
P-doped NiCo ₂ O ₄ /rGO	5	92.9	88.5%@10000 cycles	[3]
NiCo ₂ O ₄ // NiCo ₂ O ₄	2	73.1	86%@500 cycles	[4]
NiCo ₂ O ₄ @N-doped Carbon//AC	5	105.1	97.3%@15000 cycles	[5]
CNTs@NiCo LDH//rGO-Fe ₂ O ₃	2	97.1	93.5%@1000 cycles	[6]
NiCo ₂ O ₄ -CNT//AC	5	95	81.2%@5000 cycles	[7]
NiCo ₂ O ₄ @GQDs//AC	4	75	71.8%@3000 cycles	[8]
Ni(OH) ₂ //AC	1	64	75.3%@7000 cycles	[9]
NiO@Co ₃ O ₄ @graphene//AC	5	74.2	84.3%@10000 cycles	[10]
NiCoO ₂ /Ni//AC	10	70.8	90.5%@20000 cycles	[11]
CC/NiCo ₂ O ₄ @NiO/graphene	4	99.8	95.2%@10000 cycles	[12]
NiCo ₂ O ₄ /NiO/Co ₃ O ₄ //AC	1	100	83%@2000 cycles	[13]
Co ₉ S ₈ @NiCo ₂ O ₄ /AC	8	62.1	88.9%@6000 cycles	[14]
NiCo ₂ O ₄ //carbonized melamine	5	87.8	83.6%@10000 cycles	[15]
NiCo ₂ O ₄ /CoMoO ₄ //AC	4	49.27	71.4%@9000 cycles	[16]
NiCo ₂ O ₄ //superactivated carbon	5	21	87%@10000 cycles	[17]
NiCo ₂ O ₄ //graphene hydrogel	2	230	92%@5000 cycles	[18]
NiCo ₂ O ₄ //AC	0.25	82.5	90%@2000 cycles	[19]
NiCo ₂ O ₄ //PD-PC carbon	5	114.6	95.5%@5000 cycles	[20]
NiMoO ₄ /NiO//AC	0.5	95	95.5%@5000 cycles	[21]
NiCo ₂ O ₄ @rGO//rGO	6	61.2	81.1%@10000 cycles	[22]
NiCo ₂ O ₄ /graphene	5	62.2	70.5%@10000 cycles	[23]
Ni _x Co _{3-x} O ₄ //graphene hydrogel	1	130	80%@5000 cycles	[24]

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